

## Description

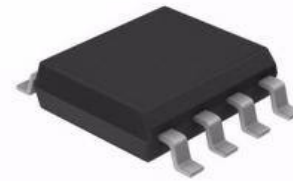
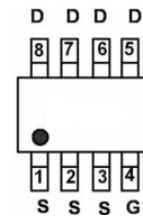
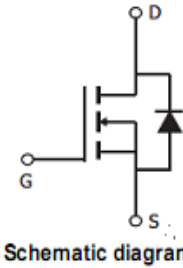
The G08N06S uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

## General Features

- |           |                             |                             |       |
|-----------|-----------------------------|-----------------------------|-------|
| $V_{DSS}$ | $R_{DS(ON)}$<br>@ 10V (Typ) | $R_{DS(ON)}$<br>@ 4.5V(Typ) | $I_D$ |
| 60V       | 24 m $\Omega$               | 30m $\Omega$                | 6A    |
- High density cell design for ultra low  $R_{dson}$
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high  $E_{AS}$
- Excellent package for good heat dissipation
- RoHS Compliant

## Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply



SOP-8 top view

## Ordering Information

Part Number	Marking	Case	Packaging
G08N06S	G08N06	SOP-8	4000pcs/Reel

## Absolute Maximum Ratings ( $T_A=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	6	A
Drain Current-Continuous( $T_C=100^{\circ}C$ )	$I_D (100^{\circ}C)$	4.2	A
Pulsed Drain Current	$I_{DM}$	32	A
Maximum Power Dissipation	$P_D$	2	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	$^{\circ}C$

## Thermal Characteristic

Thermal Resistance, Junction-to-Ambient <sup>(Note 2)</sup>	$R_{\theta JA}$	62.5	$^{\circ}C/W$
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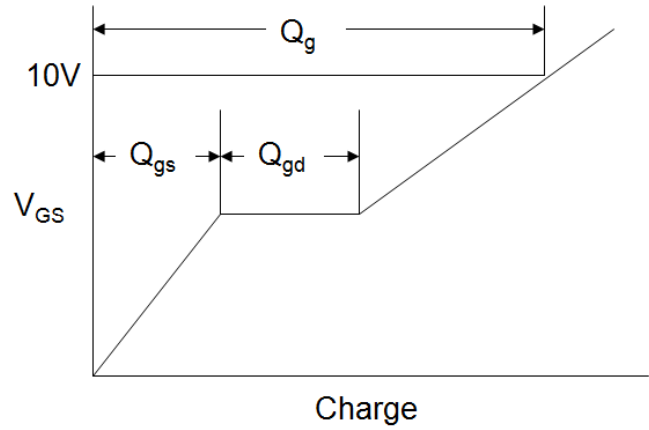
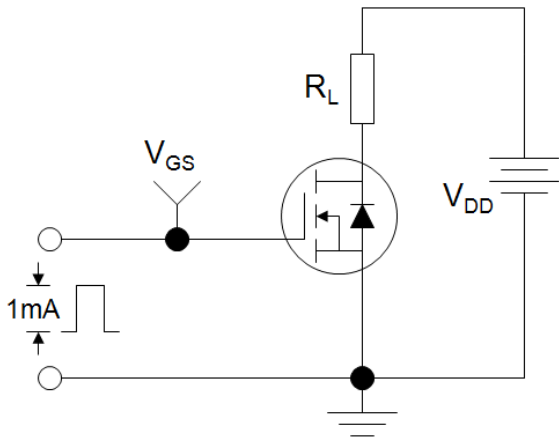
**Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	60	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA
<b>On Characteristics</b> (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1	1.7	2.5	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =3A,	-	24	30	mΩ
	R <sub>DS(ON)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =3A,	-	30	40	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =5V, I <sub>D</sub> =3A	11	-	-	S
<b>Dynamic Characteristics</b> (Note4)						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V, F=1.0MHz	-	979	-	pF
Output Capacitance	C <sub>oss</sub>		-	120	-	pF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	100	-	pF
<b>Switching Characteristics</b> (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =30V, R <sub>L</sub> =6.7Ω V <sub>GS</sub> =10V, R <sub>G</sub> =3Ω	-	5.2	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	3	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	17	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	2.5	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =30V, I <sub>D</sub> =5A, V <sub>GS</sub> =10V	-	22	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	3.3	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	5.2	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =3A,	-	-	1.2	V
Diode Forward Current (Note 2)	I <sub>S</sub>		-	-	5	A
Forward Turn-On Time	t <sub>on</sub>	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

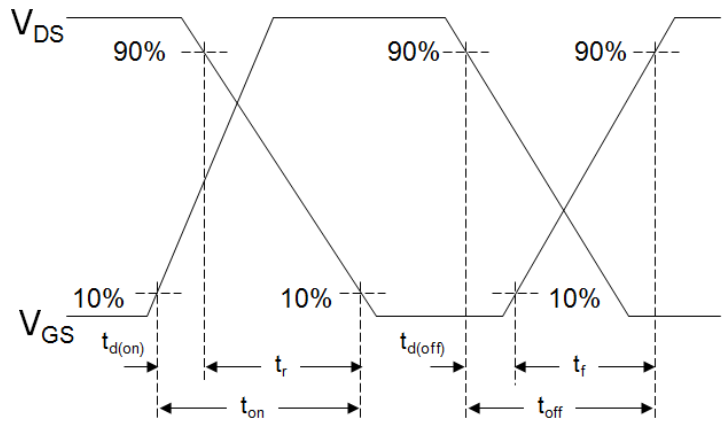
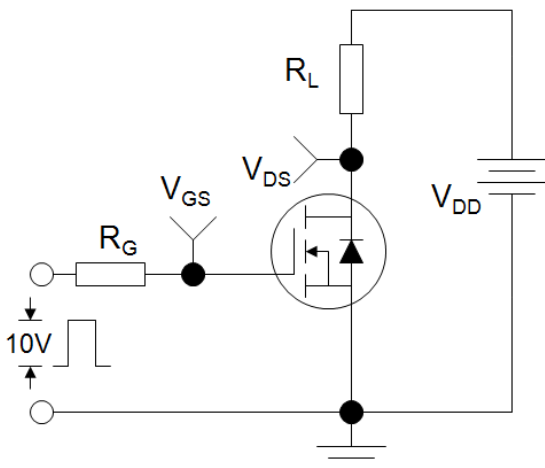
**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. EAS condition: T<sub>J</sub>=25°C, V<sub>DD</sub>=30V, V<sub>G</sub>=10V, L=0.5mH, R<sub>g</sub>=25Ω

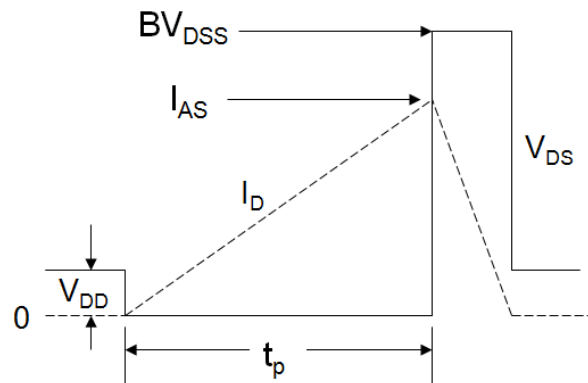
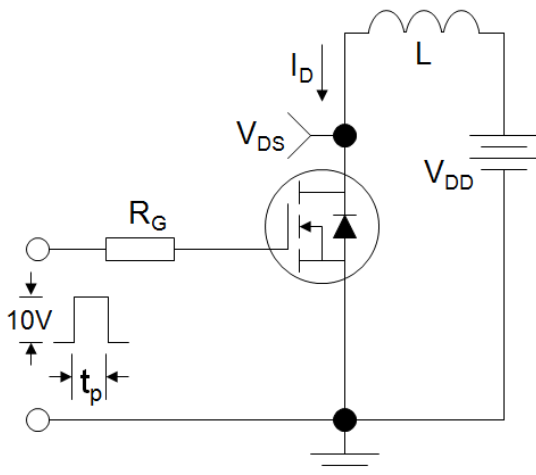
**Gate Charge Test Circuit**



**Switch Time Test Circuit**



**EAS Test Circuit**



Typical Electrical and Thermal Characteristics (Curves)

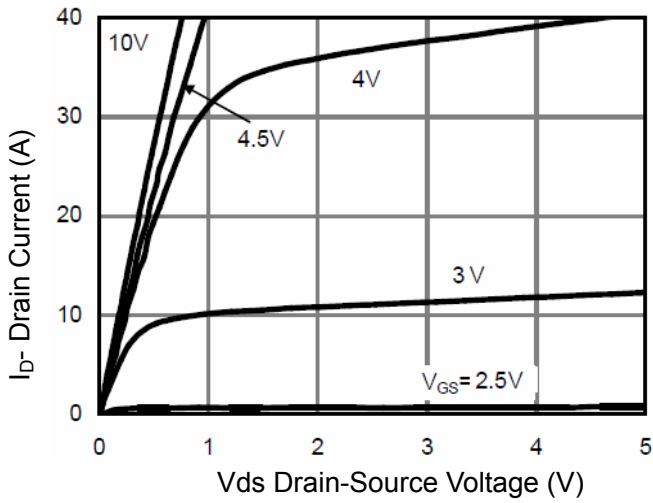


Figure 1 Output Characteristics

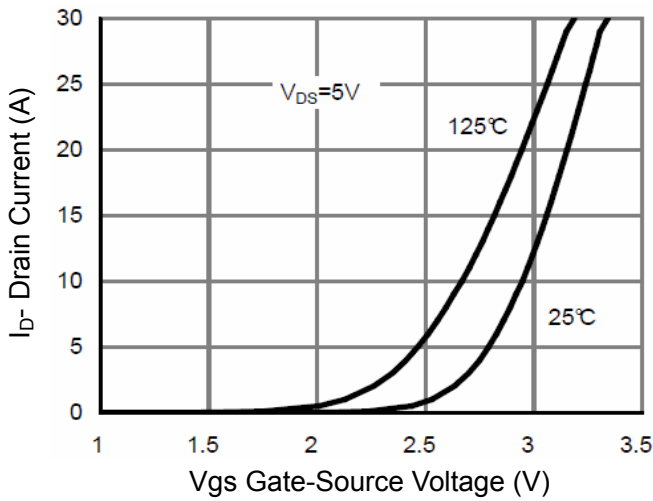


Figure 2 Transfer Characteristics

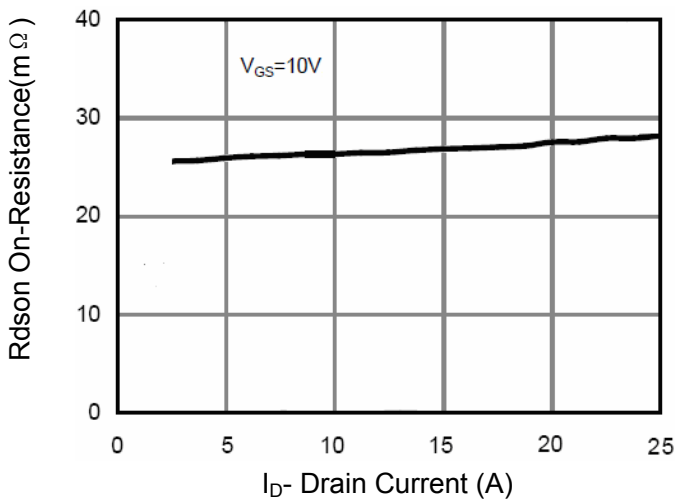


Figure 3 Rdson- Drain Current

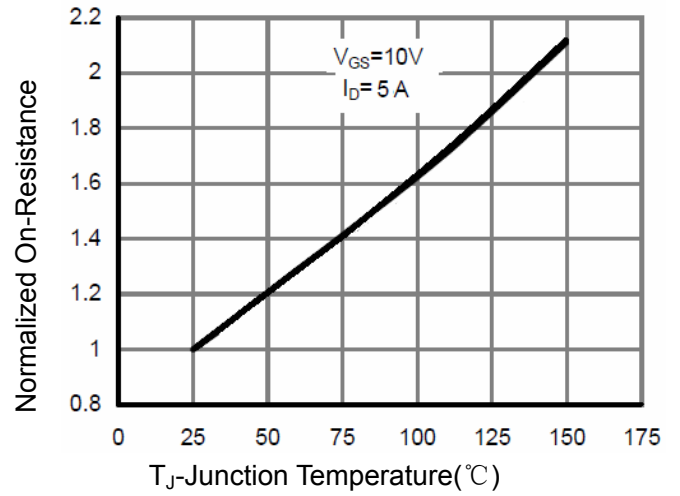


Figure 4 Rdson-Junction Temperature

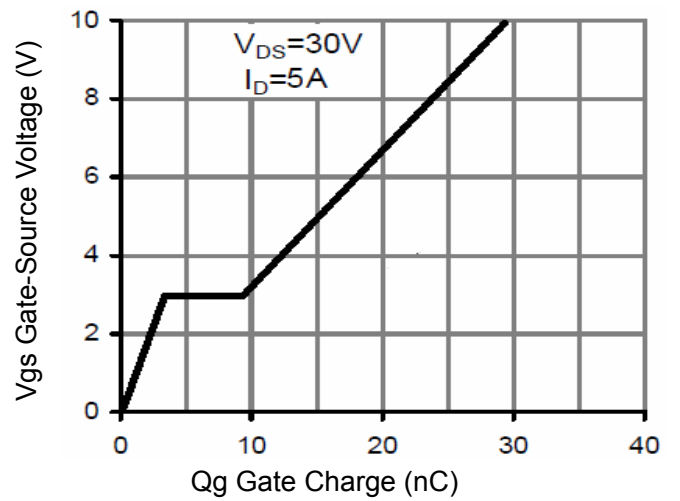


Figure 5 Gate Charge

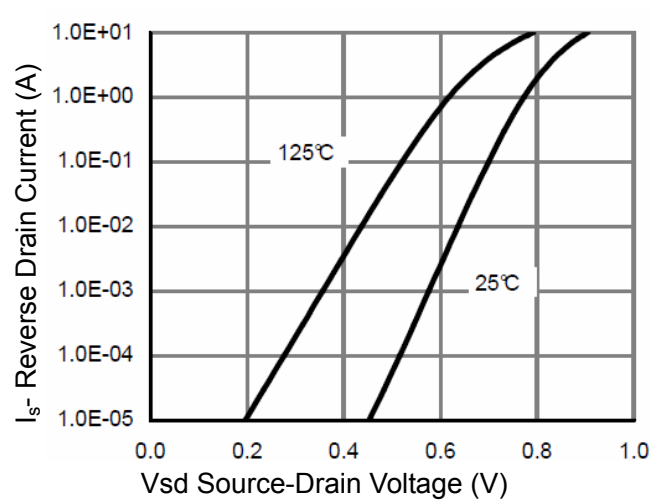


Figure 6 Source- Drain Diode Forward

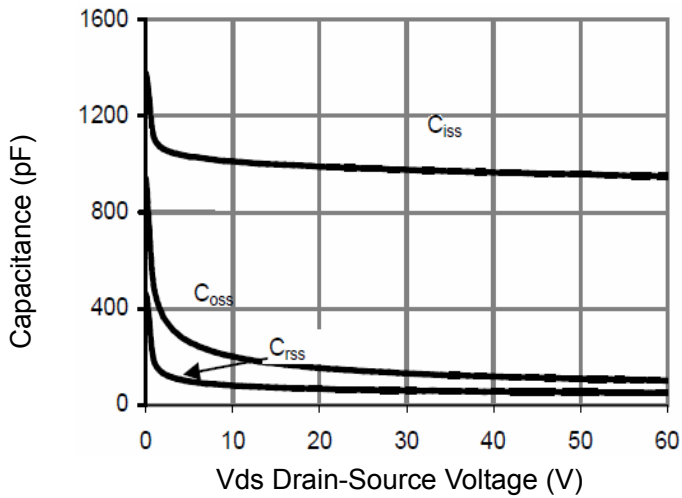


Figure 7 Capacitance vs Vds

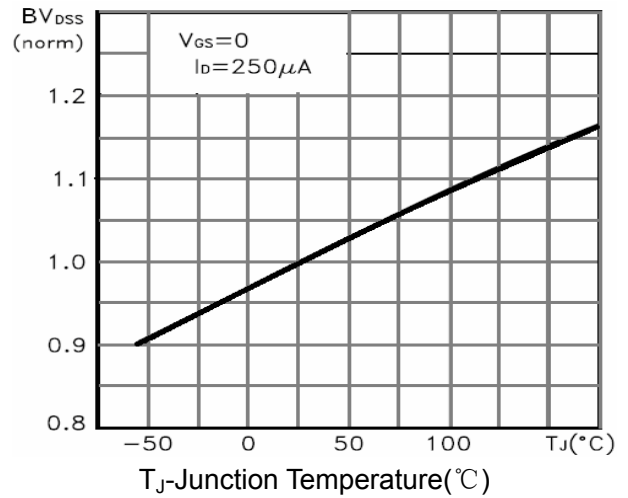


Figure 9  $BV_{DSS}$  vs Junction Temperature

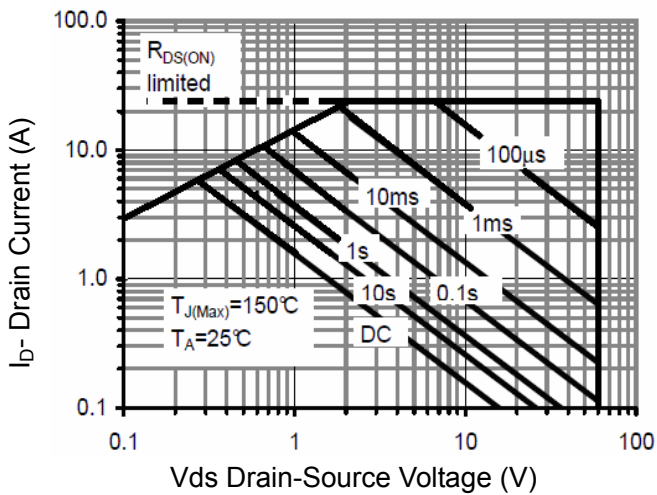


Figure 8 Safe Operation Area

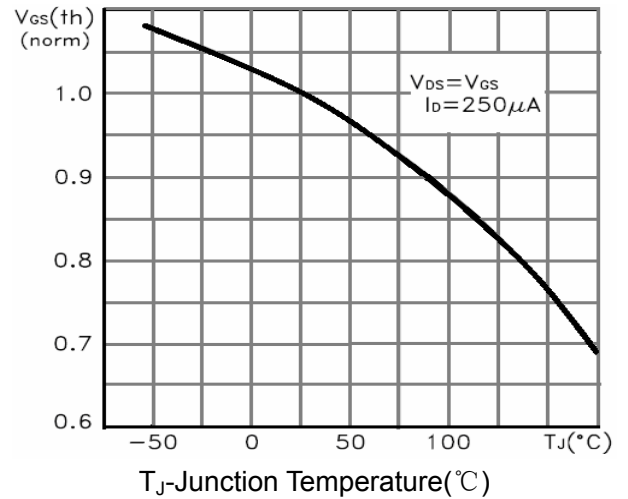


Figure 10  $V_{GS(th)}$  vs Junction Temperature

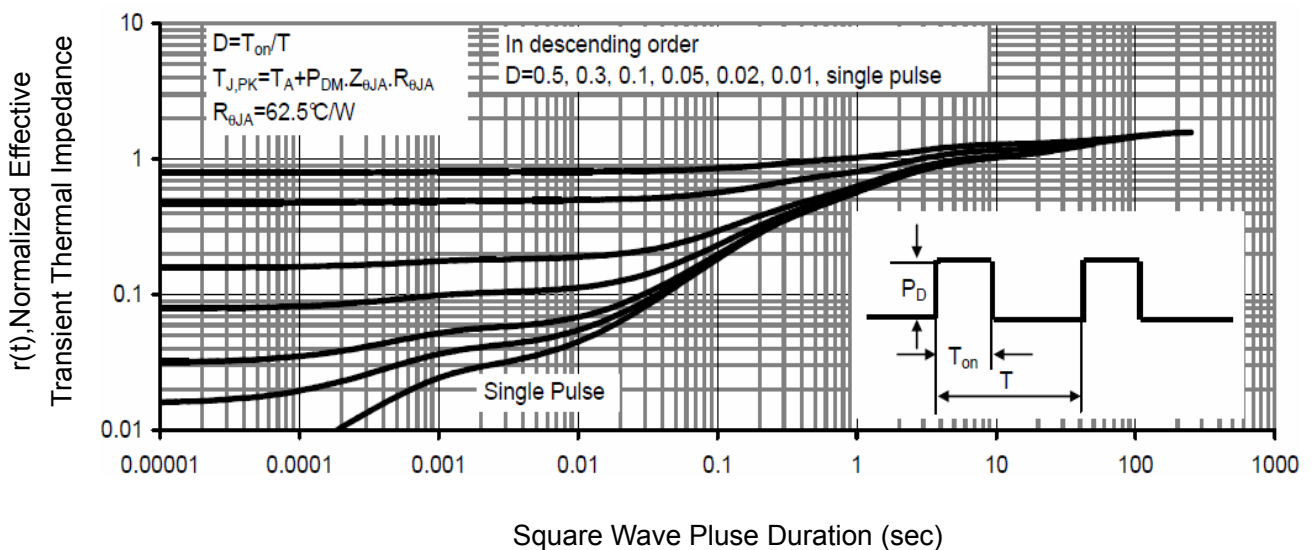
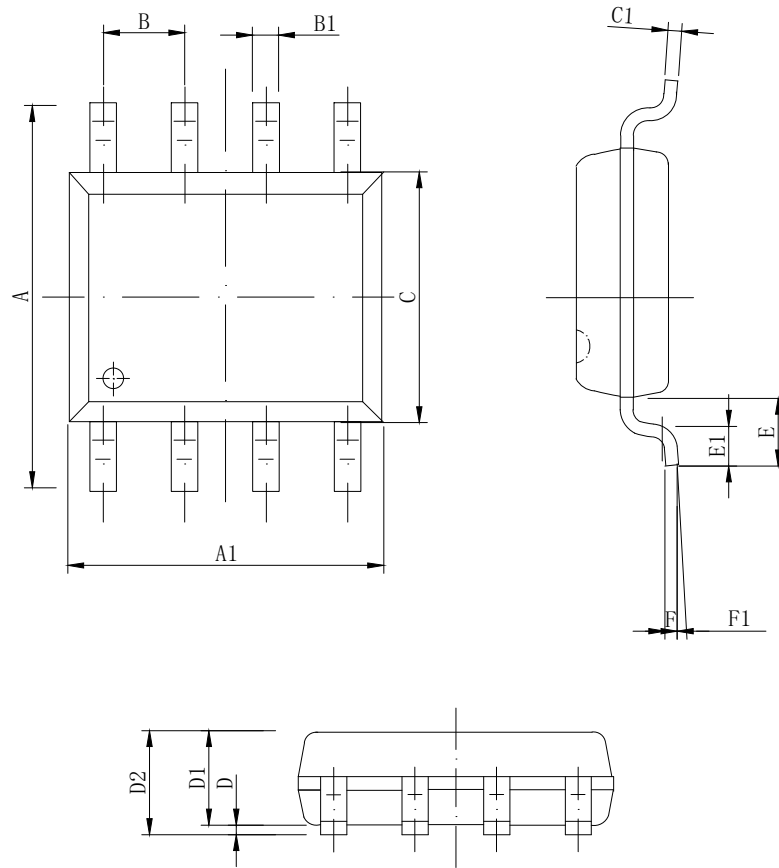


Figure 11 Normalized Maximum Transient Thermal Impedance

**SOP-8 Package information**



DIM	MIN	NOM	MAX
A	5.800	6.000	6.200
A1	4.800	4.900	5.000
B	1.270BSC		
B1	0.35 ^ 8x	0.40 ^ 8x	0.45 ^ 8x
C	3.780	3.880	3.980
C1	-	0.203	0.253
D	0.050	0.150	0.250
D1	1.350	1.450	1.550
D2	1.500	1.600	1.700
E	1.060 REF		
E1	0.400	0.700	0.100
F	0.250BSC		
F1	2°	4°	6°

All Dimensions in mm